BTA312G-600CT

3Q Hi-Com Triac

11 April 2016 **Product data sheet**

1. General description

Planar passivated high commutation three quadrant triac in a SOT226A (I2PAK) plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series CT" triac will commutate the full RMS current at the maximum rated junction temperature ($T_{j(max)}$ = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)
- High voltage capability
- Less sensitve gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant

3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

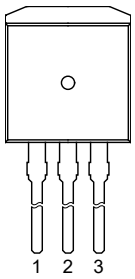
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq$ 118 °C; Fig. 1; Fig. 2; Fig. 3		-	-	12	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5		-	-	100	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms		-	-	110	A
T_j	junction temperature			-	-	150	°C
Static characteristics							

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{GT}	gate trigger current	V_D = 12 V; I_T = 100 mA; T2+ G+; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 100 mA; T2+ G-; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 100 mA; T2- G-; T_j = 25 °C; Fig. 7		-	-	35	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	35	mA
V_T	on-state voltage	I_T = 15 A; T_j = 25 °C; Fig. 10		-	-	1.6	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		300	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		8	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 **I2PAK (SOT226A)**	 *sym051*
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA312G-600CT	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226A

7. Marking

Table 4. Marking codes

Type number	Marking code
BTA312G-600CT	BTA312G-600CT

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq$ 118 °C; Fig. 1; Fig. 2; Fig. 3		-	12	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5		-	100	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms		-	110	A
I^2t	I^2t for fusing	t_p = 10 ms; sine-wave pulse		-	50	A²s
dI_T/dt	rate of rise of on-state current	I_G = 70 mA		-	100	A/µs
I_{GM}	peak gate current	t = 20 µs		-	2	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	150	°C

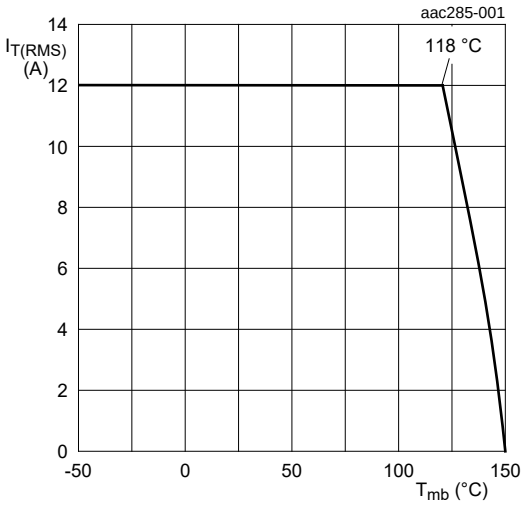
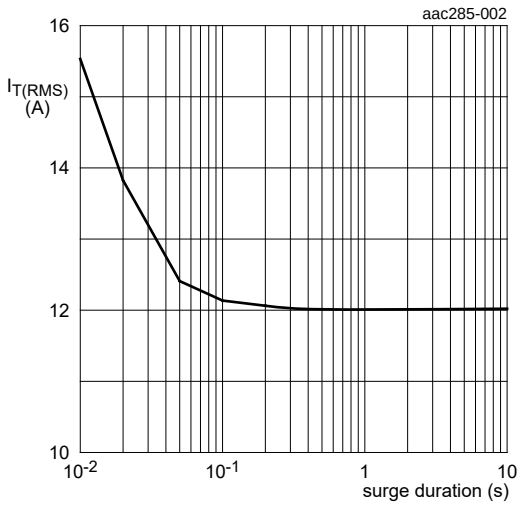
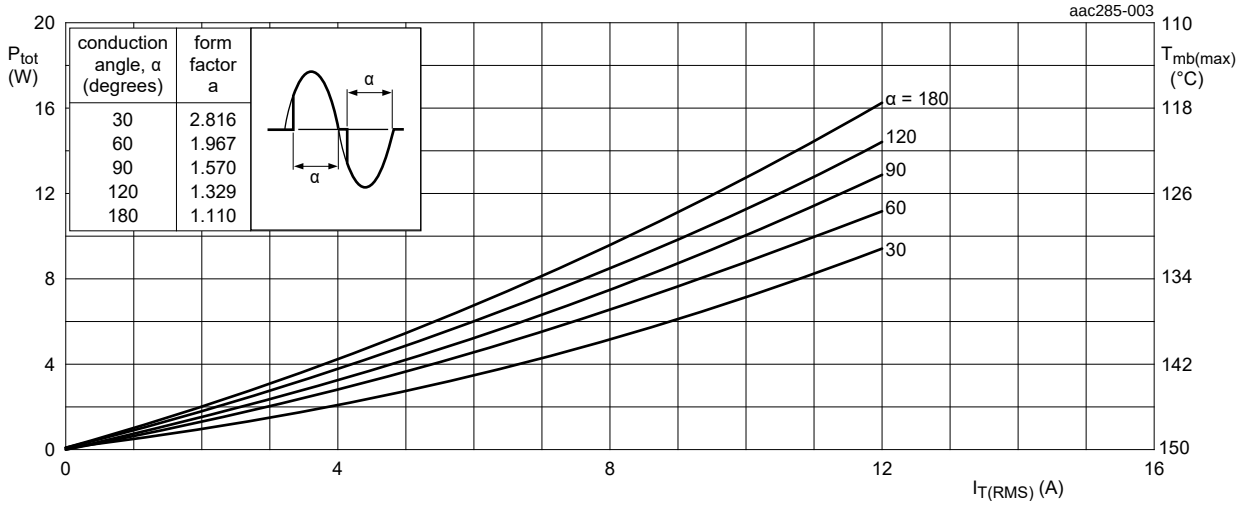


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_{mb} = 118 °C

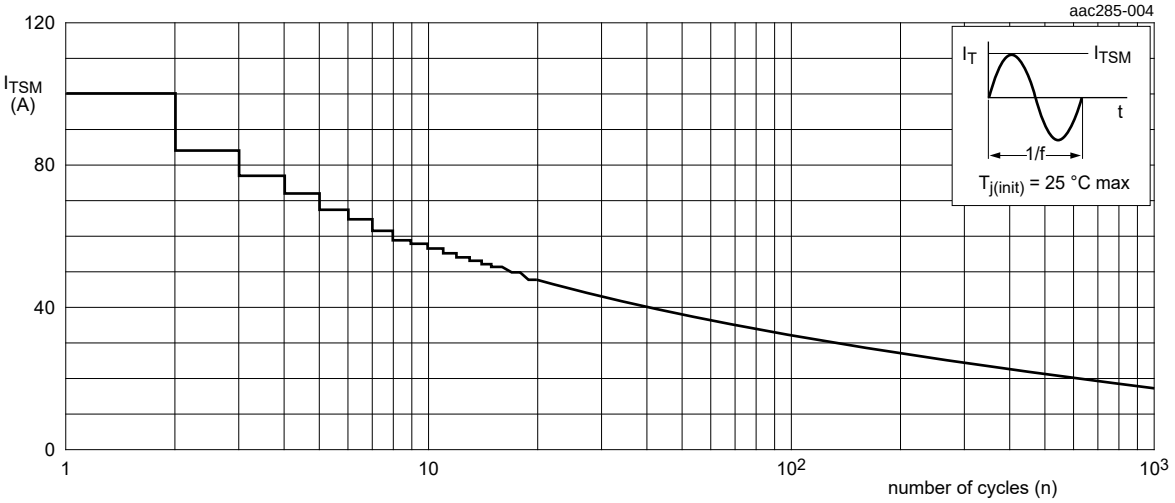
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

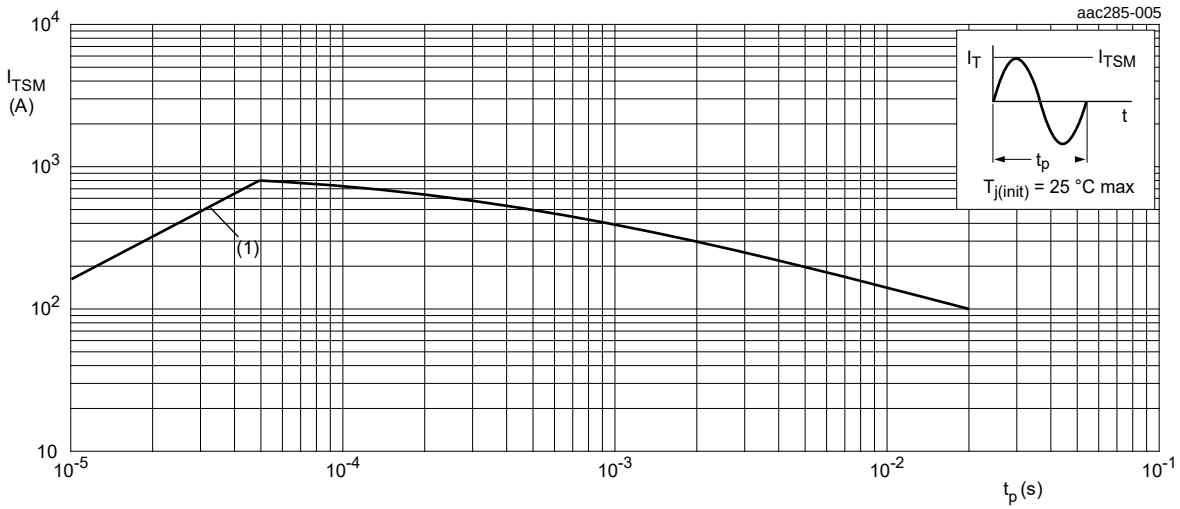
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$ ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; Fig. 6		-	-	2.4	K/W
		full cycle; Fig. 6		-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

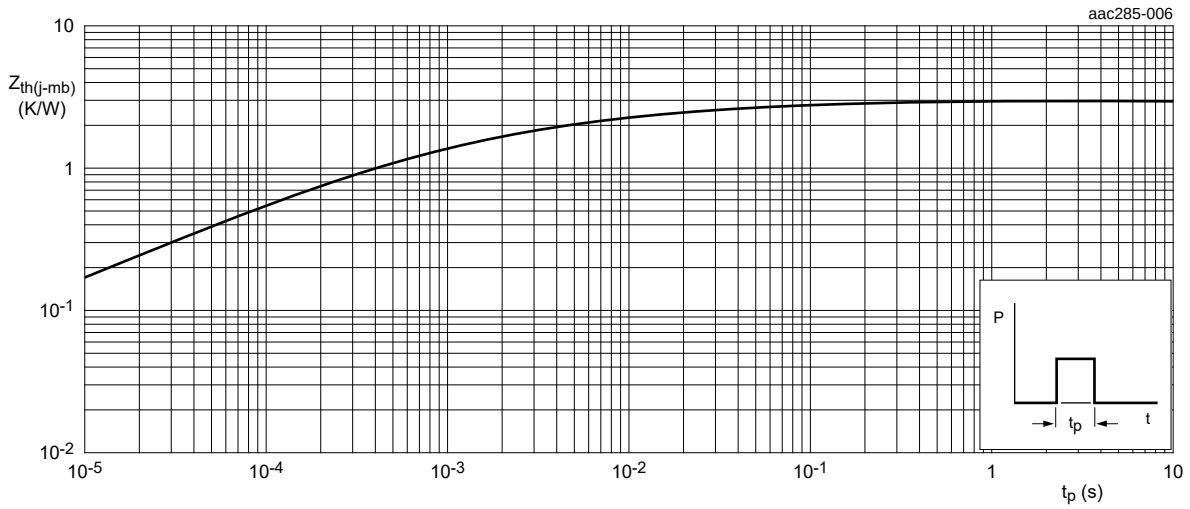
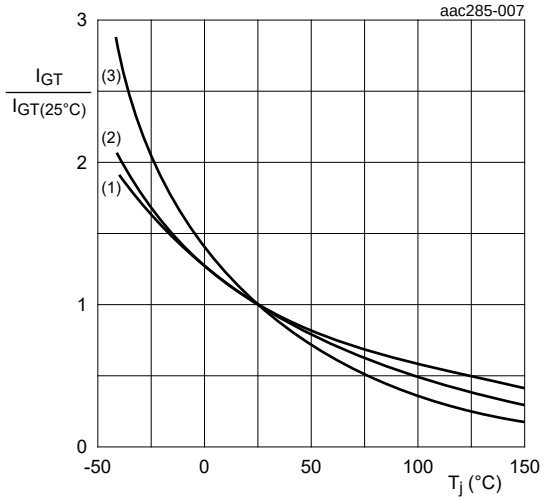


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 100 mA; T2+ G+; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 100 mA; T2+ G-; T_j = 25 °C; Fig. 7		-	-	35	mA
		V_D = 12 V; I_T = 100 mA; T2- G-; T_j = 25 °C; Fig. 7		-	-	35	mA
I_L	latching current	V_D = 12 V; I_G = 100 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	50	mA
		V_D = 12 V; I_G = 100 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	60	mA
		V_D = 12 V; I_G = 100 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	50	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	35	mA
V_T	on-state voltage	I_T = 15 A; T_j = 25 °C; Fig. 10		-	-	1.6	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 100 mA; T_j = 25 °C; Fig. 11		-	0.8	1	V
		V_D = 400 V; I_T = 100 mA; T_j = 150 °C; Fig. 11		0.2	0.45	-	V
I_D	off-state current	V_D = 600 V; T_j = 25 °C		-	-	10	µA
		V_D = 600 V; T_j = 150 °C		-	0.4	2	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		300	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		8	-	-	A/ms



(1) T2+ G+
(2) T2+ G-
(3) T2- G-

Fig. 7. Normalized gate trigger current as a function of junction temperature

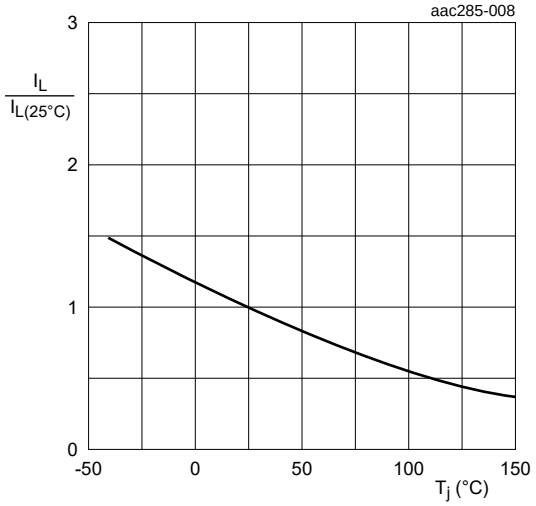


Fig. 8. Normalized latching current as a function of junction temperature

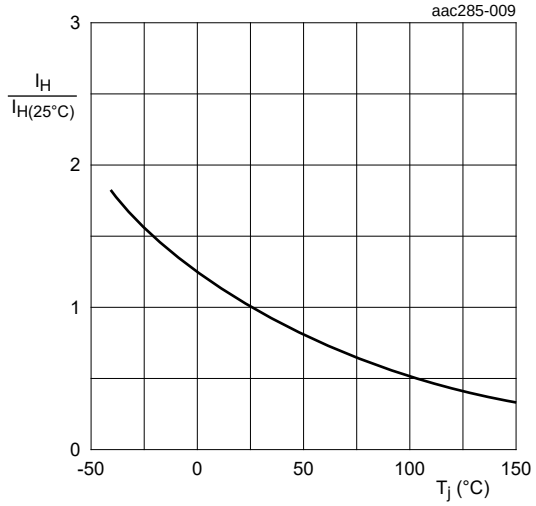
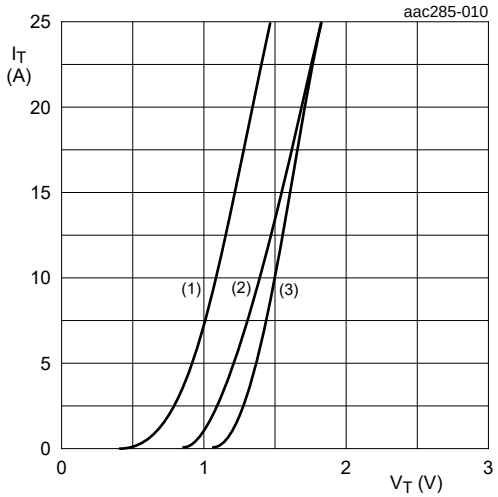


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.037 V; R_s = 0.034 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

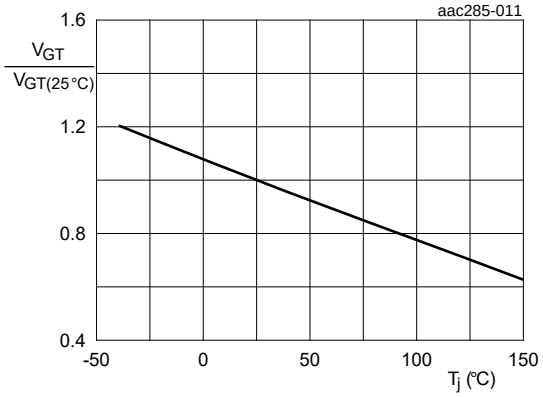
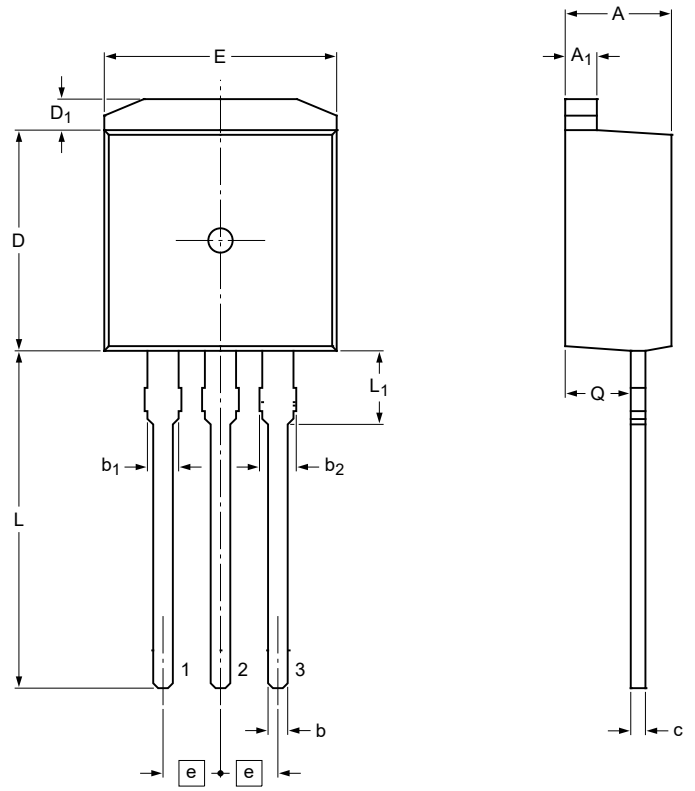
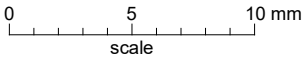


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262 **SOT226A**





Dimensions

Unit		A	A_1	b	b_1	b_2	c	D	D_1	E	e	L	L_1	Q
mm	max	4.7	1.40	0.95	1.40	1.7	0.65	9.4	1.32	10.30	2.54 (REF)	15.0	3.0 (REF)	2.6
	nom													
	min	4.3	1.15	0.70	1.14	1.3	0.45	8.6	1.02	9.65		12.5		2.2

sot226a_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT226A		TO-262				~~09-08-17~~ 09-08-25

Fig. 12. Package outline I2PAK (SOT226A)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 11 April 2016

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105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

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